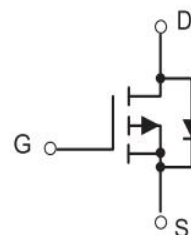


MAIN CHARACTERISTICS

I_D	-110 A
V_{DSS}	-40 V
$R_{DS(ON)-typ}$ (@ $V_{GS}=-10V$)	3.8mΩ



FEATURES

- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED
- 100% ΔV_{ds} TESTED

APPLICATIONS

- Load Switch
- PWM Application
- Power Management



Product specification classification

Part Number	Package	Mode Name	Pack
LT110P04AD	TO-252	LT110P04AD	Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continue Drain Current	I_D	-110	A
Pulsed Drain Current (Note1)	I_{DM}	-440	A
Single Pulsed Avalanche Energy	E_{AS}	272	mJ
Power Dissipation	P_D	89	W
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-50 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.4	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62	°C/W

Note1: Pulse test: 300 μ s pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	BV_{DSS}	-40	-	-	V
Drain-Source Leakage Current	$V_{DS} = -40 \text{ V}, V_{GS} = 0 \text{ V}$	I_{DSS}	-	-	-1	μA
Gate Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	$V_{GS(th)}$	-1.1	-	-2.2	V
Drain-Source On-State Resistance	$V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$	$R_{DS(on)}$	-	3.8	5	m Ω
	$V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}$		-	5.4	7	m Ω
Input Capacitance	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$	C_{iss}	-	5705	-	pF
Output Capacitance		C_{oss}	-	654	-	pF
Reverse Transfer Capacitance		C_{rss}	-	555	-	pF
Turn-on Delay Time(Note2)	$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, R_G = 6 \Omega, I_D = -20 \text{ A}$	$t_{d(ON)}$	-	13	-	ns
Rise Time(Note2)		t_r	-	78	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	194	-	ns
Fall Time(Note2)		t_f	-	110	-	ns
Total Gate Charge(Note2)	$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$	Q_G	-	118	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	14	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	27	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	-110	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	-440	A
Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -10 \text{ A}, T_J = 25$	V_{SD}	-	-	-1.2	V
Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_S = -20 \text{ A},$	t_{rr}	-	22	-	ns

Reverse Recovery Charge	$di/dt=100A/\mu s$	Qrr	-	15	-	nC
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Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

RATINGS AND CHARACTERISTIC CURVES

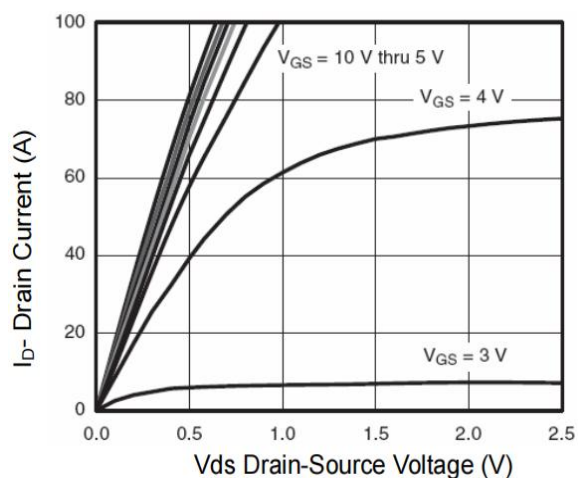


Figure 1 Output Characteristics

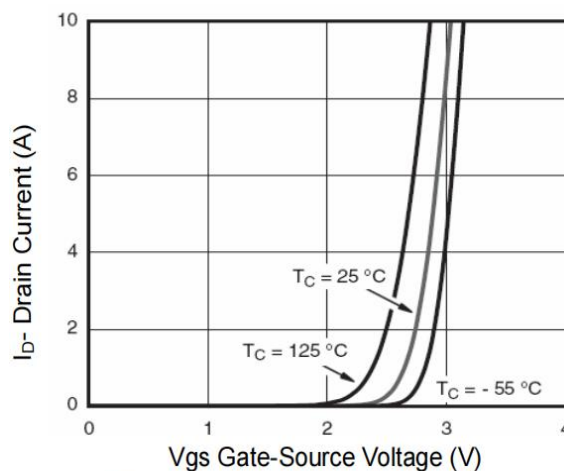


Figure 2 Transfer Characteristics

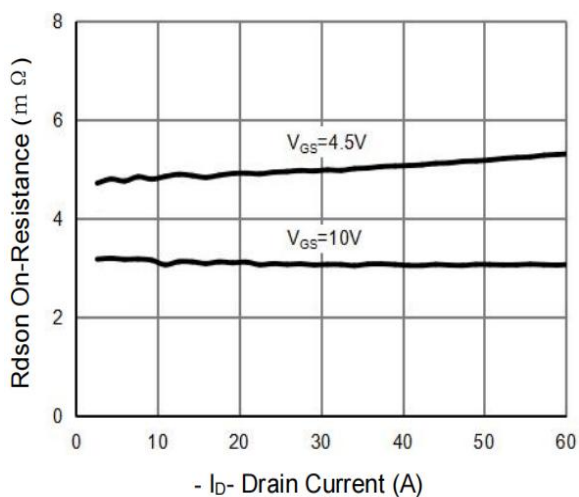


Figure 3 Rdson- Drain Current

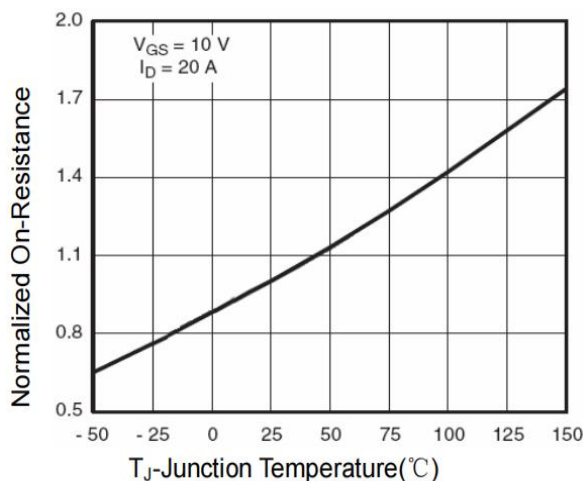
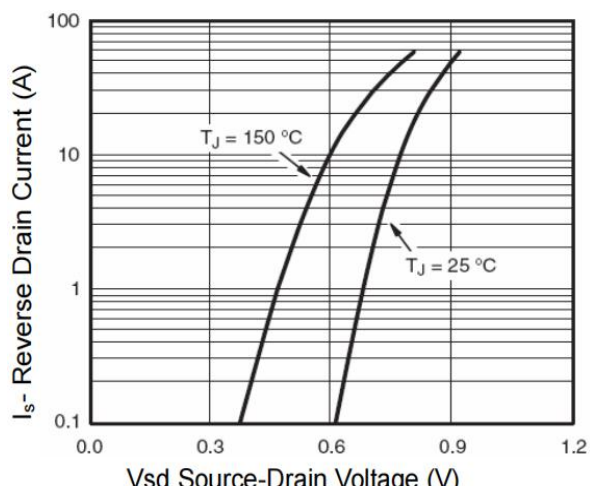
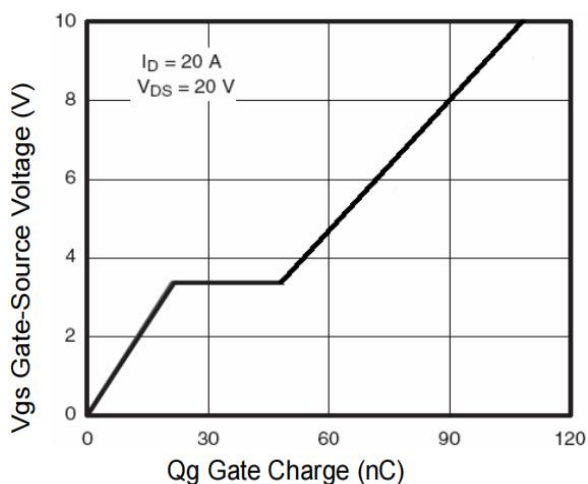


Figure 4 Rdson-Junction Temperature





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LX MICRO
Qy Gate Charge (nC)

Figure 5 Gate Charge

LT110P04AD

P-Channel Trench Power MOSFET

V_{SD} Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward

RATINGS AND CHARACTERISTIC CURVES

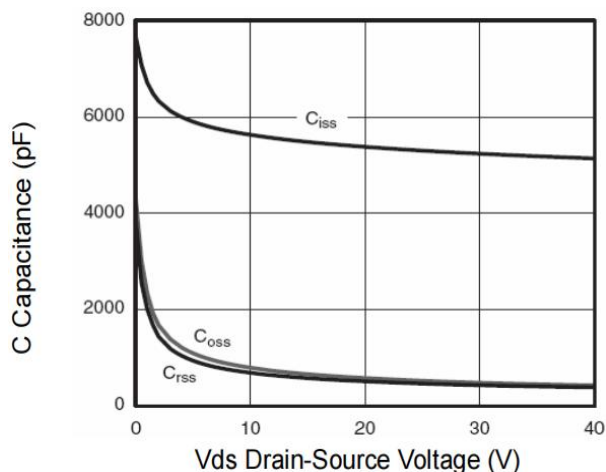


Figure 7 Capacitance vs Vds

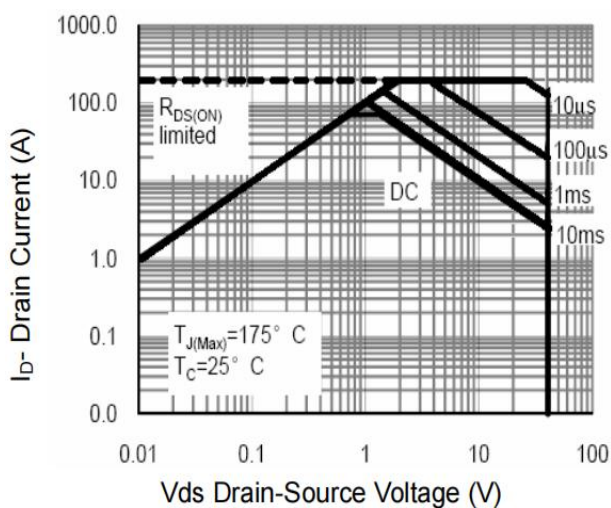


Figure 8 Safe Operation Area

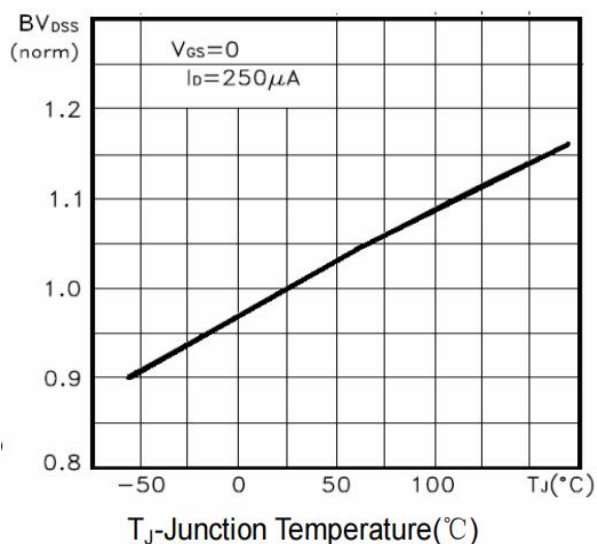


Figure 9 BV_{DSS} vs Junction Temperature

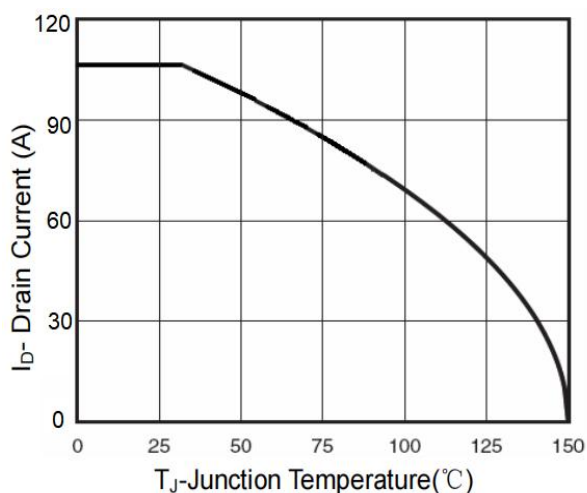
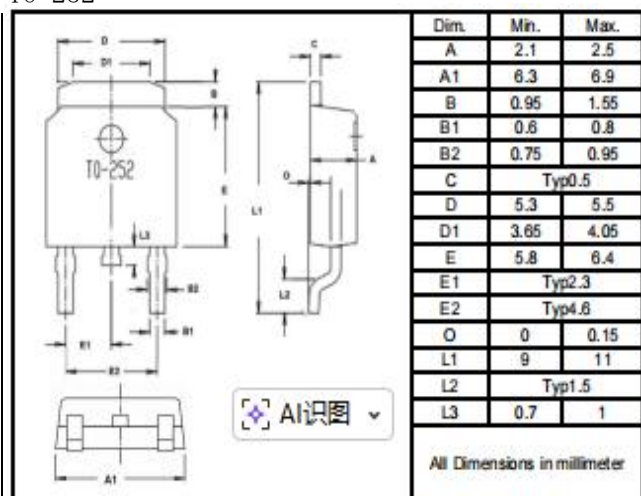


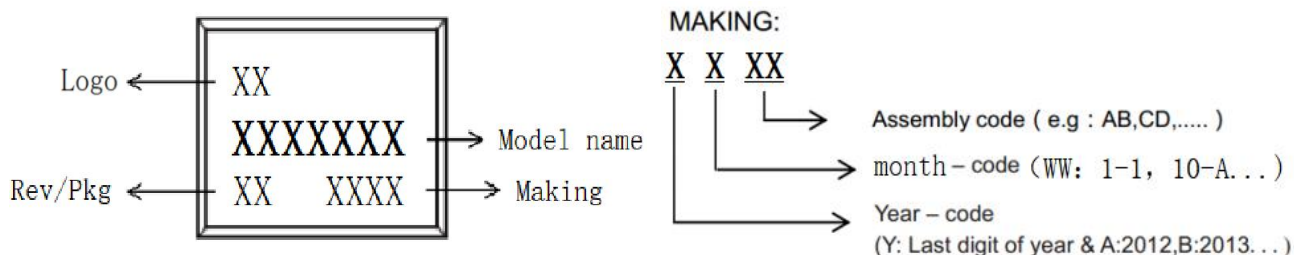
Figure 10 I_D Current Derating vs Junction Temperature

Package Outline Dimensions millimeters

TO-252



Marking on the body



packing instruction

PKG	最小包装	内盒	外箱
TO-252			
	2500pcs/盘	5000pcs/盒	25000pcs/箱

Notice

All product,product specifications and data are subject to change without notice to improve.The right to explain is owned by LINGXUN electronics company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying poer exceeding normal ratedpoer; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.



LT110P04AD

P-Channel Trench Power MOSFET

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.